AB67 Colpitt's Oscillator

> Operating Manual Ver.1.1

An ISO 9001 : 2000 company



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RoHS Compliance



Scientech Products are RoHS Complied.

RoHS Directive concerns with the restrictive use of Hazardous substances (Pb, Cd, Cr, Hg, Br compounds) in electric and electronic equipments.

Scientech products are "Lead Free" and "Environment Friendly".

It is mandatory that service engineers use lead free solder wire and use the soldering irons upto (25 W) that reach a temperature of 450° C at the tip as the melting temperature of the unleaded solder is higher than the leaded solder.

Introduction

AB67 is a compact, ready to use **Colpitt's Oscillator** experiment board. This is useful for students to understand functionality of **Colpitt's Oscillator**. It can be used as stand alone unit with external DC Power Supply or can be used with **Scientech Analog Lab ST2612** which has built in DC Power Supply, AC Power Supply, function generator, modulation generator, continuity tester, toggle switches, and potentiometers.

List of Boards :

Model	Name
AB01	Diode characteristics (Si, Zener, LED)
AB02	Transistor characteristics (CB NPN)
AB03	Transistor characteristics (CB PNP)
AB04	Transistor characteristics (CE NPN)
AB05	Transistor characteristics (CE PNP)
AB06	Transistor characteristics (CC NPN)
AB07	Transistor characteristics (CC PNP)
AB08	FET characteristics
AB09	Rectifier Circuits
AB10	Wheatstone bridge
AB11	Maxwell's Bridge
AB12	De Sauty's Bridge
AB13	Schering Bridge
AB14	Darlington Pair
AB15	Common Emitter Amplifier
AB16	Common Collector Amplifier
AB17	Common Base Amplifier
AB18	RC-Coupled Amplifier
AB19	Cascode Amplifier
AB20	Direct Coupled Amplifier
AB21	Class A Amplifier
AB22	Class B Amplifier (push pull emitter follower)
AB23 AB24	Class C Tuned Amplifier
AB24 AB25	Transformer Coupled Amplifier
AD25	Phase Locked Loop (FM Demodulator & Frequency Divider / Multiplier)
AB26	FET Amplifier
AB20 AB27	Voltage Controlled Oscillator
AB28	Multivibrator (Mono stable/Astable)
AB29	F-V and V-F Converter
AB30	V-I and I-V Converter
AB31	Zener Voltage Regulator
AB32	Transistor Series Voltage Regulator
AB32 AB33	Transistor Shunt Voltage Regulator
	Tunoiotoi onune voitugo regunutoi

AB67 AB35 DC Ammeter **AB37** DC Ammeter (0-2mA) **AB39** Instrumentation Amplifier **AB41** Differential Amplifier (Transistorized) Operational Amplifier (Inverting / Non-inverting / Differentiator) **AB42 AB43** Operational Amplifier (Adder/Scalar) Operational Amplifier (Integrator/ Differentiator) **AB44 AB45** Schmitt Trigger and Comparator **AB49** K Derived Filter Active filters (Low Pass and High Pass) **AB51** Active Band Pass Filter **AB52 AB54** Tschebyscheff Filter **AB56** Fiber Optic Analog Link Owen's Bridge **AB57 AB58** Anderson's Bridge **AB59** Maxwell's Inductance Bridge **AB64** RC – Coupled Amplifier with Feedback Wien Bridge Oscillators **AB66** Hartley Oscillator **AB68 AB80 RLC Series and RLC Parallel Resonance AB82** Thevenin's and Maximum Power Transfer Theorem **AB83 Reciprocity and Superposition Theorem AB84** Tellegen's Theorem **AB85** Norton's theorem **AB88 Diode Clipper AB89 Diode Clampers** Two port network parameter **AB90 AB91** Optical Transducer (Photovoltaic cell) **AB92** Optical Transducer (Photoconductive cell/LDR) **AB93 Optical Transducer (Phototransistor)** Temperature Transducer (RTD & IC335) **AB96 AB97** Temperature Transducer (Thermocouple) DSB Modulator and Demodulator **AB101 AB102** SSB Modulator and Demodulator **AB106** FM Modulator and Demodulator

and many more.....

Theory

Oscillators are circuits that produce specific, periodic waveforms such as square, triangular, sawtooth, and sinusoidal. They can be made from some of the active or passive devices like transistors, FETs and Op-Amps in combination with devices such as resistors, capacitors, and inductors, to generate the output.

There are two main classes of oscillator; relaxation and sinusoidal. Relaxation oscillators generate the triangular, sawtooth and other nonsinuoidal waveforms. Sinusoidal oscillators consist of amplifiers with external components used to generate oscillation, or crystals that internally generate the oscillation. The focus here is on sine wave oscillators. Sine wave oscillators are used as references or test waveforms by many circuits.

An oscillator is a type of feedback amplifier in which part of the output is fed back to the input via a feedback circuit. If the signal fed back is of proper magnitude and phase, the circuit produces alternating currents or voltages. Two requirements for oscillation are

- 1. The magnitude of the loop gain $A_v B$ must be at least 1, and
- 2. The total phase shift of the loop gain A_vB must be equal to 0° or 360° . If the amplifier causes a phase shift of 180° , the feedback circuit must provide an additional phase shift of 180° so that the total phase shift around the loop is 360° .

Colpitt's Oscillator :

The **Colpitt's Oscillator** is one of the simplest and best known oscillators and is used extensively in circuits, which work at radio frequencies. Figure1 shows the basic **Colpitt's Oscillator** circuit configuration. The transistor is in voltage divider bias which sets up Q-point of the circuit. In the circuit note that V_{out} is actually the AC voltage across C2. This voltage is fed back to the base and sustains oscillations developed across the tank circuit, provided there is enough voltage gain at the oscillation frequency.

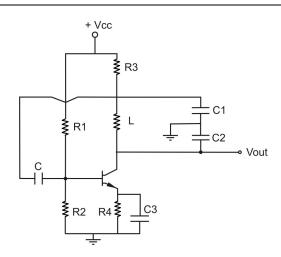


Figure 1

The resonant frequency of the **Colpitt's Oscillator** can be calculated from the tank circuit used. We can calculate the approximately resonant frequency as

Resonant Frequency (fr) =
$$\frac{1}{2p\sqrt{LC}}$$
 (1)

Here, the capacitance used is the equivalent capacitance the circulating current passes through. In **Colpitt's Oscillator** the circulating current passes through the series combination of C_1 and C_2 . Therefore equivalent capacitance is,

$$Cequ = \frac{C_1 C_2}{C_1 + C_2}$$

Starting condition for oscillations is

AB>1

Where,

B is approximately equal to C_1/C_2 .

The feedback should be enough to start oscillations under all conditions as different transistors, are used at varying, temperatures, voltages, etc. But the feedback should not be so large that you lose the required output. The resonant frequency can be changed by either changing the value of inductor or changing the value of capacitor but the combination of the three components should satisfy the above given two conditions for oscillation.

AB67

Experiment

Objective : Study of operation of Colpitt's Oscillator

Equipments Needed :

- 1. Analog board AB67
- 2. DC Power Supplies +12V from external source or ST2612 Analog Lab
- 3. Oscilloscope 20 MHz, Caddo 802 or equivalent
- 4. 2mm Patch Cords

Circuit diagram : Circuit used to study the operation of **Colpitt's Oscillator** is as shown in figure 2.

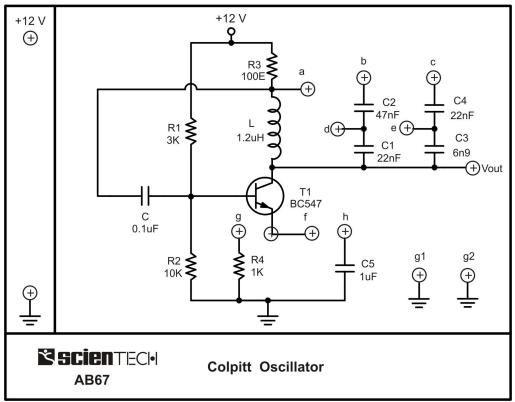


Figure 2

Procedure:

- Study of Colpitt's Oscillator proceed as follows :
- 1. Connect +12V DC Power Supply at their indicated position from external source or ST2612 Analog Lab.
- 2. Connect a patch cord between points a and b and another patch chord between points d and g1.
- **3.** Connect patch chord between points f and h and another patch chord between points g and emitter of transistor T1.
- 4. Switch 'On' the Power Supply.
- 5. Connect oscilloscope between points V_{out} and g2 on AB67 board.
- 6. Record the value of output frequency on oscilloscope.
- 7. Calculate the resonant frequency using equation 1.
- 8. Compare measured frequency with the theoretically calculated value.
- 9. Switch 'Off' the supply.
- **10.** Remove the patch chord connected between points a and b and connect it between points a and c.
- **11.** Remove the patch chord connected between points d and g1 and connect it between points e and g2.
- **12.** Follow the procedure from point 4 to 8.
- **13.** Connect +5V Supply instead of +12V Supply and follow the procedure from point 2 to point 11.

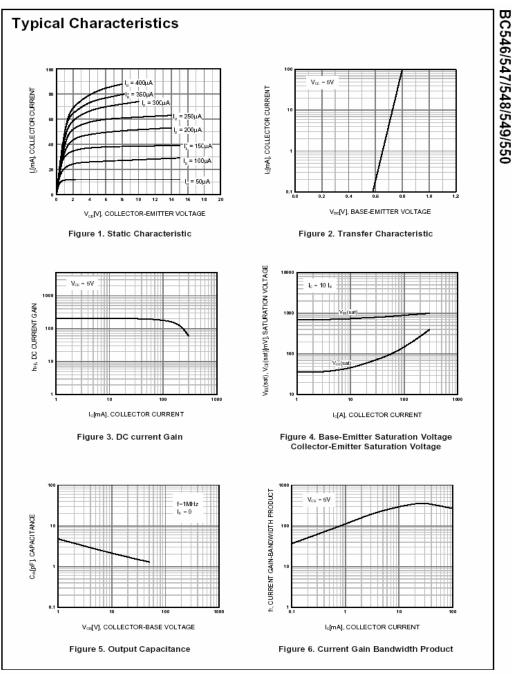
Result :

Data Sheet

		BC546/	547/	548/549/550)				
High Volta Low Nois	ng and App age: BC546, V _{CEK} e: BC549, BC550 ent to BC556 B	₀ =65∨					1		
					1 Collect	1 TO-92 Collector 2. Base 3. Emitter			
PN E	pitaxial S	ilicon Trans	istor		1. 001000	2.04	30 0. EII	itter	
nsolut	te Maximun	n Ratings _{⊺a} =25	°C upless	othenwise noted					
Symbo			meter	outerwise noted	v	alue	U	nits	
СВО		Base Voltage : BC5				80		V	
			47/550 48/549		50 30		×.		
CEO	Collector	Emitter Voltage : BC5				65		v	
520			47/550			45		V	
	Emitter B		48/549 46/547		30		_	V V	
EBO	Emitter-B		48/549/55	50		6 5		v	
Collector Current (DC)						100		mA	
Collector Power Dissipation						500		mW	
J		Temperature				150		°C	
STG	Storage	Temperature			-65	~ 150		°C	
ectric	al Characte	eristics Ta=25°C u	unless offi	erwise noted					
Symbol	-	rameter	-	Test Condition	Min.	Тур.	Max.	Units	
BO	Collector Cut-of	f Current	V _{CB} =30				15	nA	
E	DC Current Gai			/, I _C =2mA	110		800		
CE (sat)	Collector-Emitte	r Saturation Voltage		A, I _B =0.5mA nA, I _B =5mA		90 200	250 600	m∨ m∨	
_{BE} (sat)	Base-Emitter Sa	aturation Voltage		A, I _B =0.5mA		700	000	mV	
			I _C =100r	mA, I _B =5mA		900		m∨	
BE (on)	Base-Emitter O	n Voltage		(, I _C =2mA	580	660	700 720	m∨ m∨	
	Current Gain Ba	andwidth Product		/, I _C =10mA /, I _C =10mA, f=100MHz		300	720	MHz	
ob	Output Capacita		V _{CB} =10V, I _E =0, f=1MHz			3.5	6	pF	
ib	Input Capacitan			V _{EB} =0.5V, I _C =0, f=1MHz		9		pF	
F		: BC546/547/548 : BC549/550 : BC549 : BC550	f=1KHz V _{CE} =5V	/, I _C =200μΑ , R _G =2KΩ /, I _C =200μΑ Ω, f=30~15000MHz		2 1.2 1.4 1.4	10 4 4 3	dB dB dB dB	
							Ŭ		
01-1									
	ssification	A		В			С		

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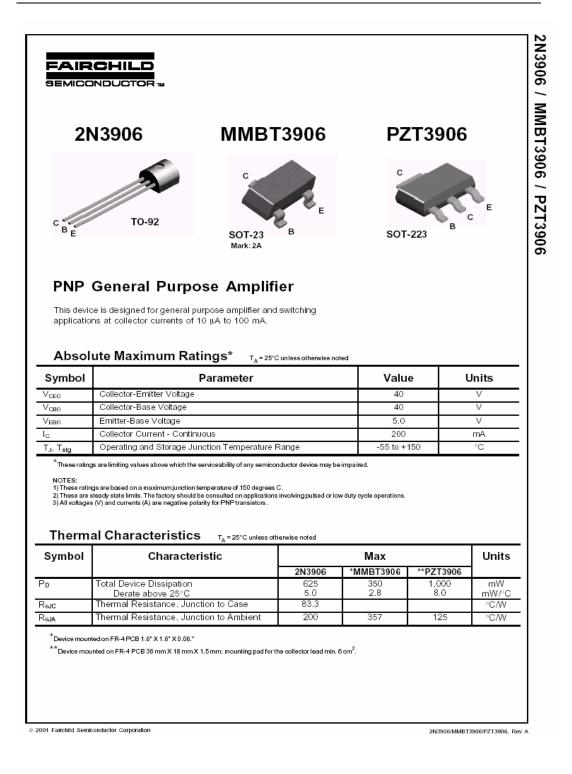


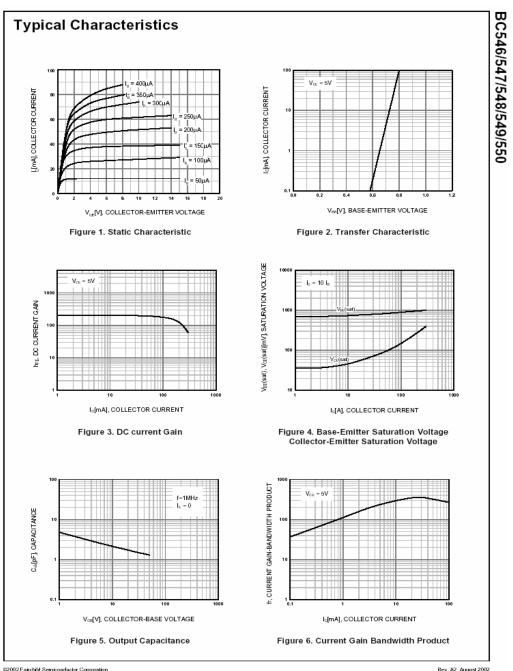
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2	N3906 N	IMBT3906	PZ	T3906		
CBE		C SOT-23 Mark: 2A	c SOT-	223 B	c	
This devi	General Purpose A	- mplifier and switching				
	ute Maximum Ratings'	P				
ymbol	Param	eter	Value	e l	Jnits v	
CEO	Collector-Emitter Voltage		40			
CBO	Collector-Base Voltage		40			
BO	Emitter-Base Voltage		5.0	5.0 V 200 mA		
	Collector Current - Continuous Operating and Storage Junction T	monoraturo Bondo	-55 to +1	50	°C	
	gs are limiting values above which the serviceabili				0	
ı, T _{stg} [*] Theseratin						
*These ratin NOTES: 1) These ratin 2) These are 3) All voltage	gs are based on a maximum junction temperature steady state limits. The factory should be consulte s (V) and currents (A) are negative polarity for PN	of 150 degrees C. I on applications involving pulsed or low Pransistors . 25°C unless otherwise noted	duty cycle operations. Max		Units	
*Theseratin NOTES: 1) These ratin 2) These are 3) All voltage Therm ymbol	gs are based on a maximum junction temperature steady state limits. The factory should be consults s (V) and currents (A) are negative polarity for PN al Characteristics T _A = Characteristic	d on applications involving pulsed or low Ptransistors. 25°C unless otherwise noted 2N3906	Мах *MMBT3906	**PZT3906	-	
*Theseratin NOTES: 1) These ratin 2) These are 3) All voltage	gs are based on a maximum junction temperature steady state limits. The factory should be consulte s (V) and currents (A) are negative polarity for PN al Characteristics T _A = Characteristic Total Device Dissipation	d on applications involving pulsed or low Ptransistors. 25°C unless otherwise noted 2N3906 625	Max *MMBT3906 350	1,000	mW	
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*Theseratin NOTES: 1)These ratin 2)These are 3)All voltage Therm ymbol	gs are based on a maximum junction temperature steady state limits. The factory should be consulte s (V) and currents (A) are negative polarity for PN al Characteristics τ _A = Characteristic Total Device Dissipation Derate above 25°C	d on applications involving pulsed or low Ptransistors. 25°C unless otherwise noted 2003906 625 5.0 Case 83.3	Max *MMBT3906 350	1,000	mW mW/≊C	

Symbol	Parameter	Test Conditions	Min	Max	Units
	RACTERISTICS	-			
(BR)CEO	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	40		V
(BR)CBO	Collector-Base Breakdown Voltage	$I_c = 10 \mu A, I_E = 0$	40		V V
(BR)EBO	Emitter-Base Breakdown Voltage Base Cutoff Current	$I_E = 10 \ \mu A, I_C = 0$ $V_{CE} = 30 \ V, V_{BE} = 3.0 \ V$	5.0	50	nA V
EX.	Collector Cutoff Current	V _{CE} = 30 V, V _{BE} = 3.0 V		50	nA
	ACTERISTICS DC Current Gain *	L = 0.1 mA V = 1.0 V	60		
FE	Do ourentoan	I _c = 0.1 mA, V _{CE} = 1.0 V I _c = 1.0 mA, V _{CE} = 1.0 V	80		
		I _c = 10 mA, V _{cE} = 1.0 V	100	300	
		I _c = 50 mA, V _{ce} = 1.0 V I _c = 100 mA, V _{ce} = 1.0 V	60 30		
CE(sat)	Collector-Emitter Saturation Voltage	I _C = 10 mA, I _B = 1.0 mA		0.25	V
BE(sat)	Base-Emitter Saturation Voltage	$I_c = 50 \text{ mA}, I_B = 5.0 \text{ mA}$ $I_c = 10 \text{ mA}, I_B = 1.0 \text{ mA}$	0.65	0.4	V
BE(Sat)	Ease Emilier Sataration Voltage	$I_{c} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$	0.00	0.95	v
	GNAL CHARACTERISTICS				
IND GE OF	Current Gain - Bandwidth Product	Ic = 10 mA, VcE = 20 V,	250		MHz
obo	Output Capacitance	f = 100 MHz V _{CB} = 5.0 V, I _E = 0,		4.5	pF
		f = 100 kHz			
ibo	Input Capacitance	VEB = 0.5 V, Ic = 0, f = 100 kHz		10.0	pF
F	Noise Figure	l _c = 100 μA, V _{CE} = 5.0 V, Rs =1.0kΩ,f=10 Hz to 15.7 kHz		4.0	dB
	NG CHARACTERISTICS				
WITCHI	Delay Time	V _{CC} = 3.0 V, V _{BE} = 0.5 V,		35	ns
	Rise Time	$I_{C} = 10 \text{ mA}, I_{B1} = 1.0 \text{ mA}$		35	ns
	Storage Time	V _{cc} = 3.0 V, I _c = 10mA		225	ns
	Fall Time	I _{B1} = I _{B2} = 1.0 mA		75	ns
NOTE: All volta	Lise Width ≤ 300 µs, DutyCycke ≤ 2.0% iges (V) and currents (A) are negative polarity for PNP tr Model 1.41f Xti=3 Eg=1.11 Vaf=18.7 Bf=180. ic=9.728p Mic=.5776 Vic=.75 Fc=.5 C1	ransistors. 7 Ne=1.5 Ise=0 Ikf=80m Xtb=1.5		Nc=2 Isc=	0 lkr=0





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Warranty

- 1. We guarantee the product against all manufacturing defects for 24 months from the date of sale by us or through our dealers. Consumables like dry cell etc. are not covered under warranty.
- 2. The guarantee will become void, if
 - a) The product is not operated as per the instruction given in the operating manual.
 - b) The agreed payment terms and other conditions of sale are not followed.
 - c) The customer resells the instrument to another party.
 - **d**) Any attempt is made to service and modify the instrument.
- **3.** The non-working of the product is to be communicated to us immediately giving full details of the complaints and defects noticed specifically mentioning the type, serial number of the product and date of purchase etc.
- 4. The repair work will be carried out, provided the product is dispatched securely packed and insured. The transportation charges shall be borne by the customer.

For any Technical Problem Please Contact us at service@scientech.bz

List of Accessories

1.	2 mm Patch Cords (Red)	1 No.
2.	2 mm Patch Cord (Blue)	
3.	2 mm Patch Cord (Black)	3 Nos.
4.	e-Manual	1 No.

Updated 30-03-2009